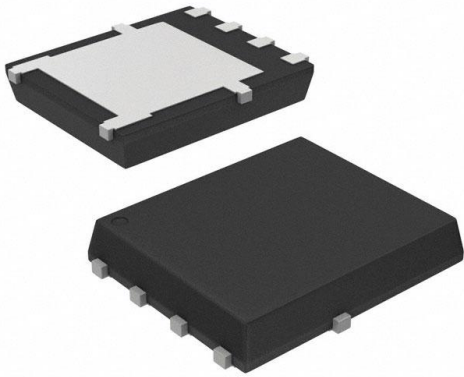


NTMFS4C020NT3G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NTMFS4C020NT3G-DG
Manufacturer	onsemi
Manufacturer Product Number	NTMFS4C020NT3G
Description	MOSFET N-CH 30V 47A/303A 5DFN
Detailed Description	N-Channel 30 V 47A (Ta), 303A (Tc) 3.2W (Ta), 134W (Tc) Surface Mount 5-DFN (5x6) (8-SOFL)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NTMFS4C020NT3G

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

30 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2.2V @ 250 μ A

Vgs (Max):

\pm 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

5-DFN (5x6) (8-SOFL)

Base Product Number:

NTMFS4

Manufacturer:

onsemi

Product Status:

Last Time Buy

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

47A (Ta), 303A (Tc)

Rds On (Max) @ Id, Vgs:

0.7mOhm @ 30A, 10V

Gate Charge (Qg) (Max) @ Vgs:

139 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

10144 pF @ 15 V

Power Dissipation (Max):

3.2W (Ta), 134W (Tc)

Mounting Type:

Surface Mount

Package / Case:

8-PowerTDFN, 5 Leads

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MOSFET – Power, Single, N-Channel, Logic Level, SO-8FL

30 V, 0.67 mΩ, 370 A
NTMFS4C020N
Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Optimized for 4.5 Gate Drive
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	30	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D	370	A
		$T_C = 25^\circ\text{C}$	P_D	161	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	57	A
		$T_A = 25^\circ\text{C}$	P_D	3.84	W
Pulsed Drain Current		$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	900	A
Operating Junction and Storage Temperature		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	110	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 35 \text{ A}$)		E_{AS}	862	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

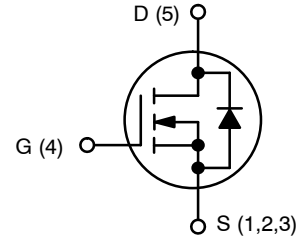
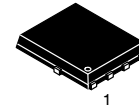
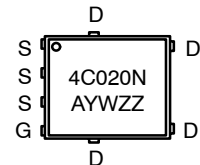
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	0.93	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	39	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	0.67 mΩ @ 10 V	370 A
	0.78 mΩ @ 6.5 V	
	0.95 mΩ @ 4.5 V	


N-CHANNEL MOSFET

**SO-8 FLAT LEAD
CASE 488AA
STYLE 1**
**MARKING
DIAGRAM**


- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4C020NT1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel

DISCONTINUED (Note 1)

NTMFS4C020NT3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
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†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

NTMFS4C020N**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			16.3		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25\ ^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.3		2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.8		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.56	0.67	m Ω
		$V_{GS} = 6.5\text{ V}, I_D = 30\text{ A}$		0.56	0.78	
		$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$		0.76	0.95	
Forward Transconductance	g_{FS}	$V_{DS} = 3\text{ V}, I_D = 30\text{ A}$		183		S
Gate Resistance	R_G	$T_A = 25\ ^\circ\text{C}$		1.0	2.5	Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$		10144	15250	pF
Output Capacitance	C_{OSS}			5073	7610	
Reverse Transfer Capacitance	C_{RSS}			148	350	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		63	105	nC
Threshold Gate Charge	$Q_{G(TH)}$			18	36	
Gate-to-Source Charge	Q_{GS}			29	58	
Gate-to-Drain Charge	Q_{GD}			13	26	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		139	230	nC

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		29		ns
Rise Time	t_r			68		
Turn-Off Delay Time	$t_{d(OFF)}$			53		
Fall Time	t_f			36		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 10\text{ A}$	$T_J = 25^\circ\text{C}$		0.73	1.1	V
			$T_J = 125^\circ\text{C}$		0.55		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 30\text{ A}$		87		ns	
Charge Time	t_a			43			
Discharge Time	t_b			44			
Reverse Recovery Charge	Q_{RR}			147		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

NTMFS4C020N

TYPICAL CHARACTERISTICS

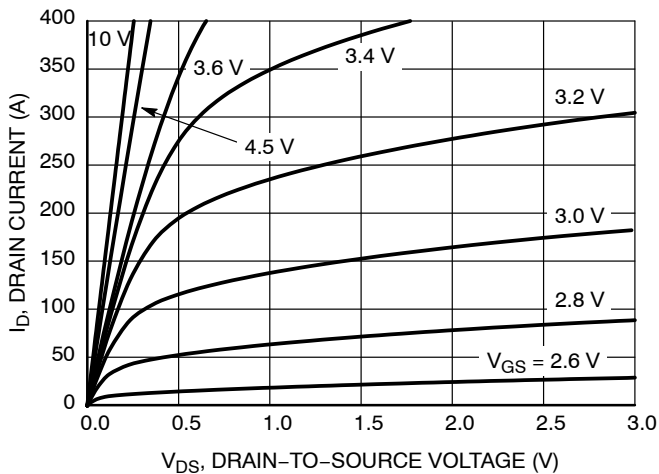


Figure 1. On-Region Characteristics

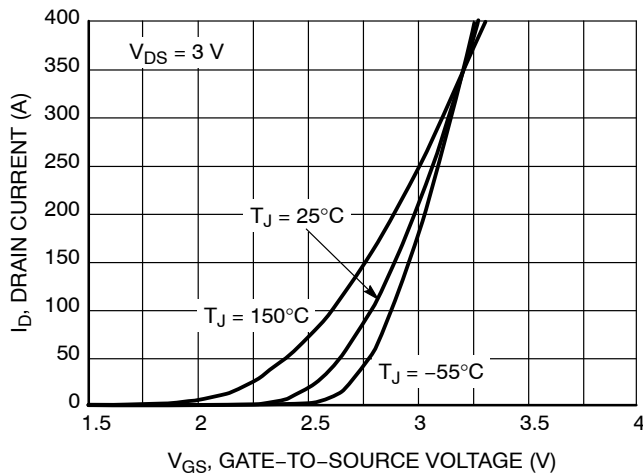


Figure 2. Transfer Characteristics

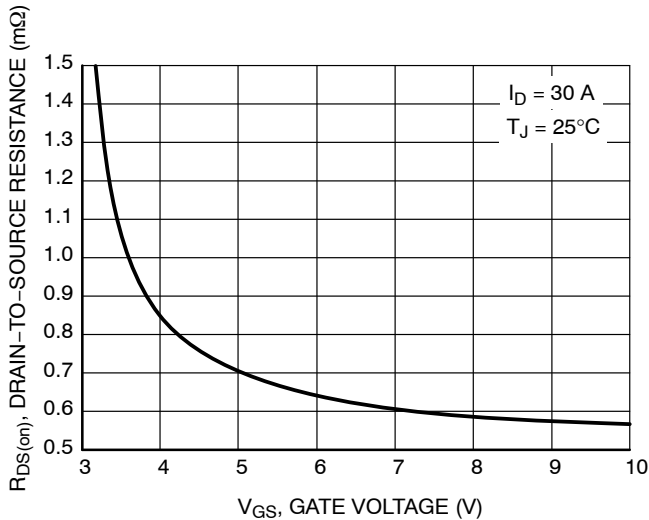


Figure 3. On-Resistance vs. Gate-to-Source Voltage

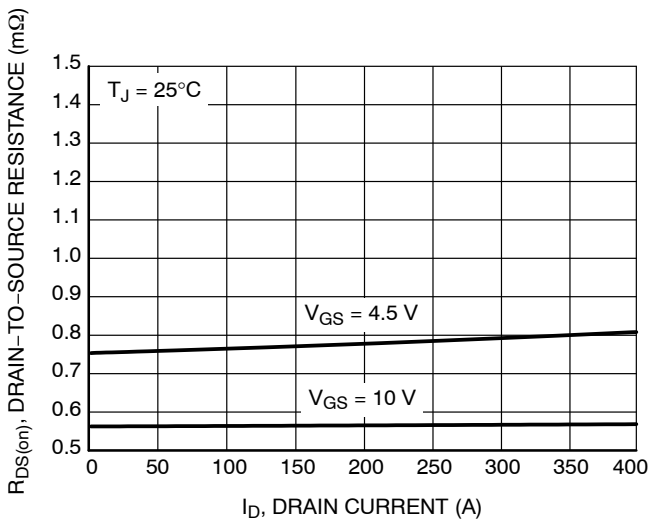


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

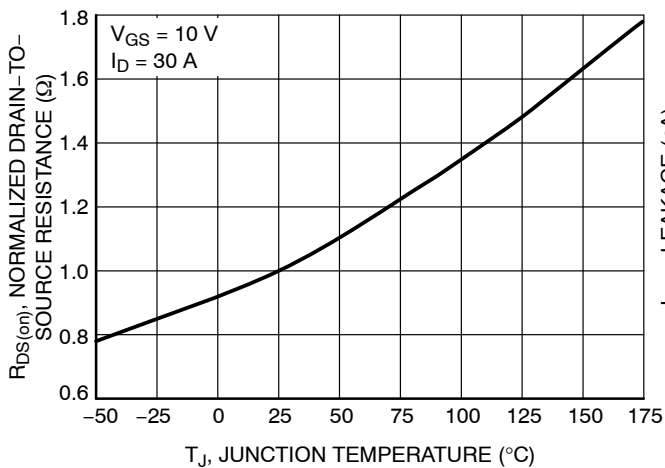


Figure 5. On-Resistance Variation with Temperature

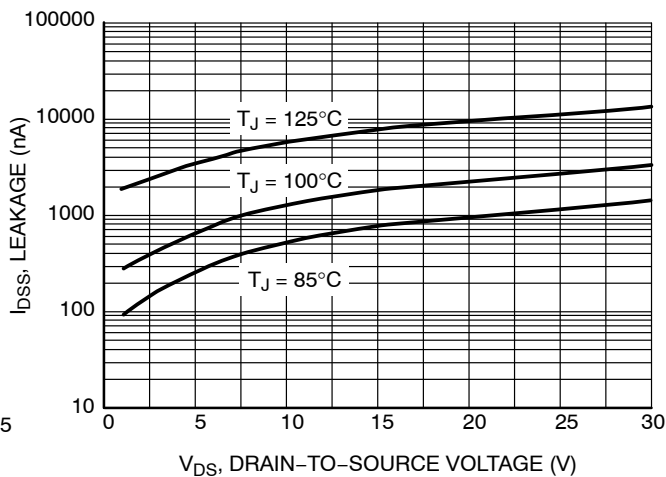


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTMFS4C020N

TYPICAL CHARACTERISTICS

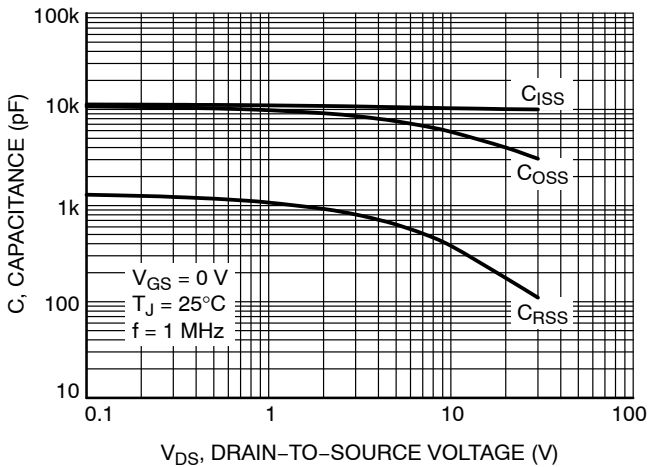


Figure 7. Capacitance Variation

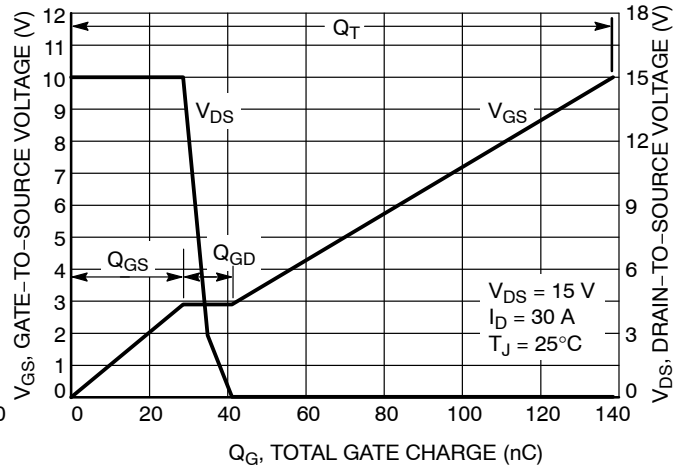


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

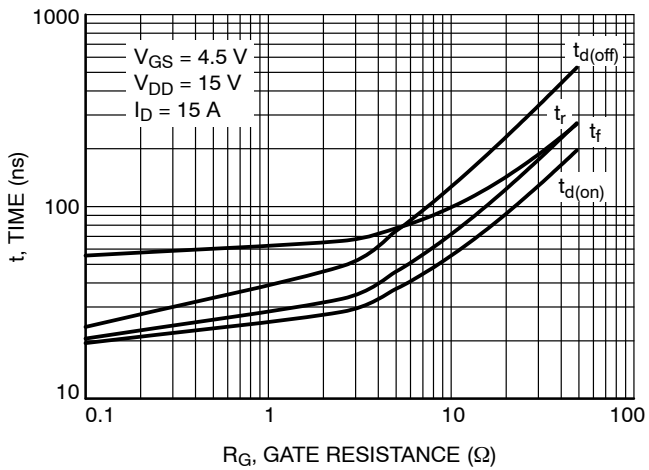


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

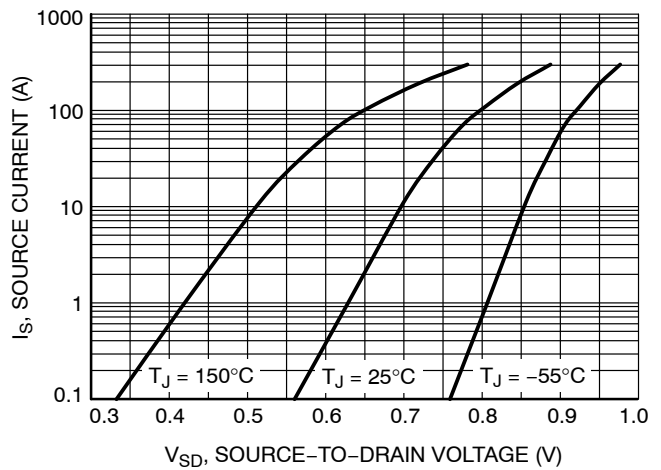


Figure 10. Diode Forward Voltage vs. Current

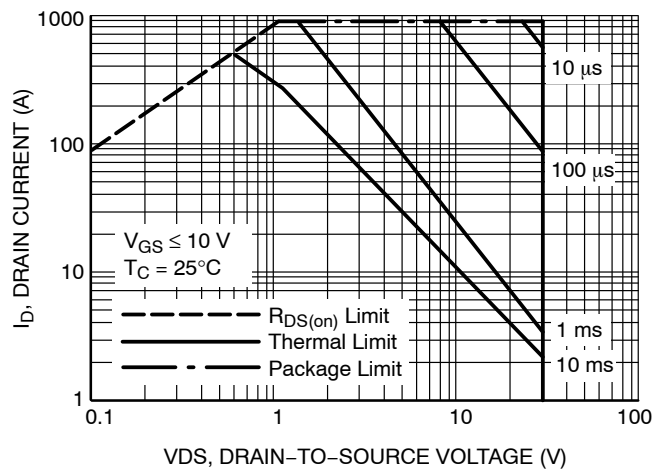


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTMFS4C020N

TYPICAL CHARACTERISTICS

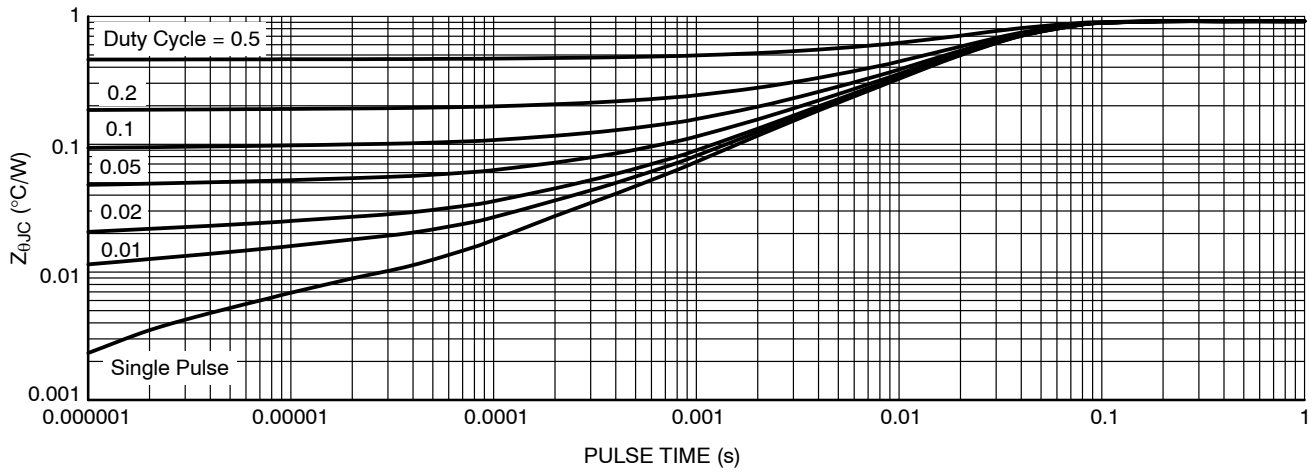


Figure 12. Thermal Resistance

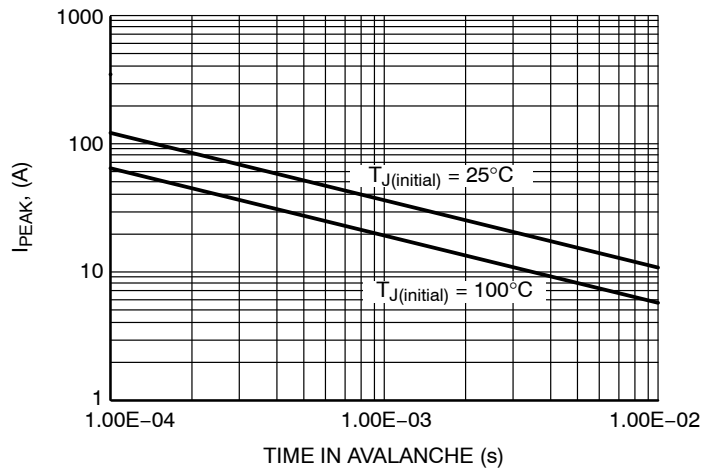


Figure 13. Avalanche Characteristics



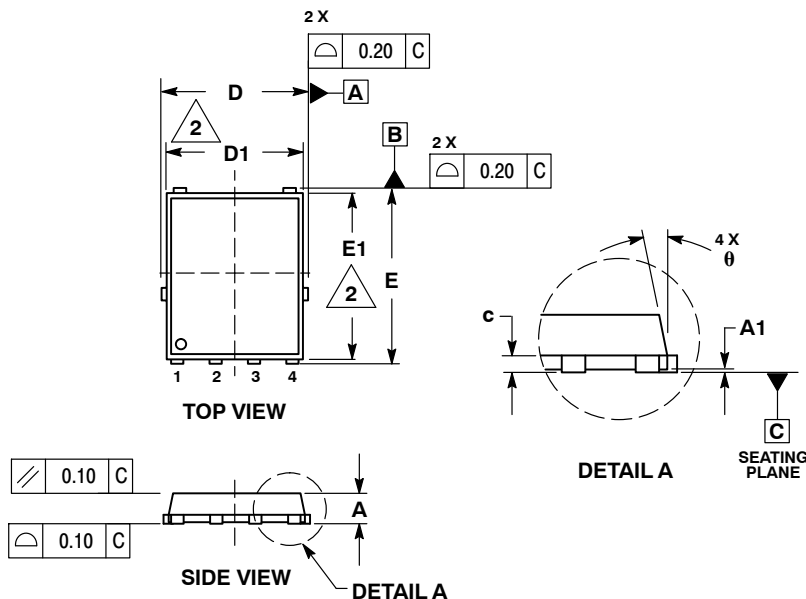
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



1
SCALE 2:1

**DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N**

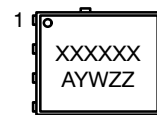
DATE 25 JUN 2018



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

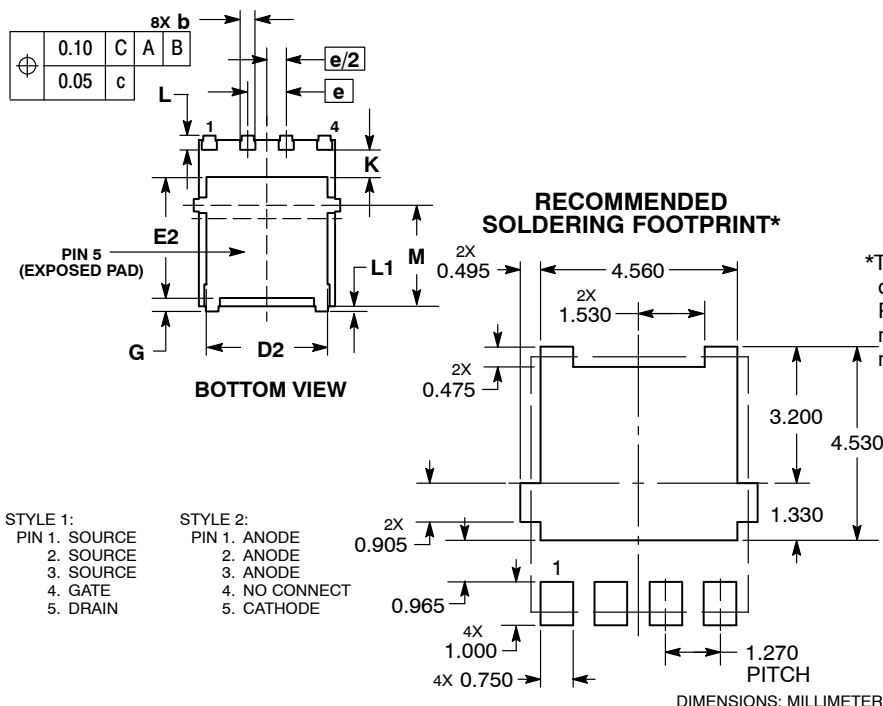
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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